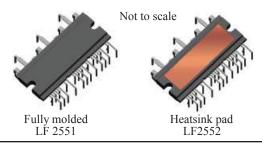


#### **Features and Benefits**

- Each half-bridge circuit consists of a pre-driver circuit that is completely independent from the others
- 10 to 30 A continuous output IPM in a small-footprint package
- Protection against simultaneous high- and low-side turning on
- Bootstrap diodes with series resistors for suppressing inrush current are incorporated
- CMOS compatible input (3.3 to 5 V)
- Designed to minimize simultaneous current through both high- and low-side IGBTs by optimizing gate drive resistors
- Integrated Fast Recovery Diode (FRD) as freewheeling diode for each IGBT
- UVLO protection with auto restart
- Thermal shutdown (TSD) with auto restart
- Fault (FO indicator) signal output at protection activation: UVLO (low side only), OCP, STP, and TSD
- Proprietary power DIP package
- UL Recognized Component (File No.: E118037)



## **Packages: Power DIP**



### Description

The SCM1240M inverter power module (IPM) devices provide a robust, highly-integrated solution for optimally controlling 3-phase motor power inverter systems and variable speed control systems used in energy-conserving designs to drive motors of residential and commercial appliances. These ICs take 85 to 253 VAC input voltage, and 10 to 30 A (continuous) output current. They can withstand voltages of up to 600 V (IGBT breakdown voltage).

The high current SCM1240M employs a new, small-footprint proprietary DIP package. The IC itself consists of all of the necessary power elements (six IGBTs), pre-drive ICs (three), and freewheeling diodes (six), needed to configure the main circuit of an inverter, as well as a bootstrap circuit (three bootstrap diodes and three boot resistors) as a high-side drive power supply. This enables the main circuit of the inverter to be configured with fewer external components than traditional designs.

Applications include residential white goods (home appliances) and commercial appliance motor control, such as:

- Air conditioner compressor motor
- Air conditioner fan motor
- Refrigerator compressor motor
- Washing machine main motor

### **Functional Block Diagram**

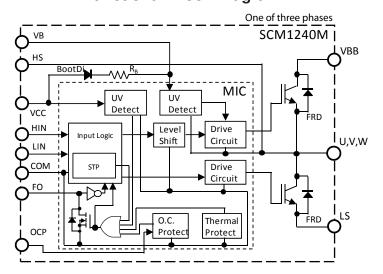


Figure 1. Diagram of one of three phases in the device.

### **Selection Guide**

			IGBT Breakdown	IGBT Saturation	<b>Output Current</b>		
Part Number	Package	Packing	Voltage, V <sub>CES</sub> (min) (V)	Voltage, V <sub>CE(sat)</sub> (typ) (V)	Continuous, I <sub>O</sub> (max) (A)	Pulsed, I <sub>OP</sub> (max) (A)	
SCM1241M	Fully Molded	10 pieces per tube	600	1.7	10	20	
SCM1243MF	Heatsink Pad	10 pieces per tube	600	1.7	15	30	
SCM1245MF	Heatsink Pad	10 pieces per tube	600	1.7	20	30	
SCM1246MF	Heatsink Pad	10 pieces per tube	600	1.7	30	45	

## **Absolute Maximum Ratings**, valid at $T_A$ = 25°C

Characteristic	Symbol		Remarks		Units
Supply Voltage	V <sub>DC</sub>	Between VBB a	nd LS1, LS2, and LS3	450	V
Supply Voltage (Surge)	V <sub>DC(surge)</sub>	Between VBB a	nd LS1, LS2, and LS3	500	V
IGBT Breakdown Voltage	V <sub>CES</sub>	V <sub>CC</sub> = 15 V, I <sub>C</sub> =	$V_{CC} = 15 \text{ V}, I_{C} = 1 \text{ mA}, V_{IN} = 0 \text{ V}$		V
Logic Supply Voltage	V <sub>CC</sub>	Between VCC a	Between VCC and COM		V
Boot-strap Voltage	V <sub>BS</sub>	Between VB and	d HS (U,V,W)	20	V
		SCM1241M	T <sub>Case</sub> = 25°C	10	Adc
Cutant Current Continuous	.	SCM1243MF	T <sub>Case</sub> = 25°C	15	Adc
Output Current, Continuous	Io	SCM1245MF	T <sub>Case</sub> = 25°C	20	Adc
		SCM1246MF	T <sub>Case</sub> = 25°C	30	Adc
		SCM1241M	Pulse Width ≤1 ms	20	Α
		SCM1243MF	Pulse Width ≤1 ms	30	Α
Output Current, Pulsed	I <sub>OP</sub>	SCM1245MF	Pulse Width ≤1 ms	30	Α
		SCM1246MF	Pulse Width ≤1 ms	45	Α
Input Voltage	V <sub>IN</sub>	HIN, LIN, and O	CP	-0.5 to 7	V
FO Terminal Voltage	V <sub>FO</sub>	Between FO an	Between FO and COM		V
		SCM1241M		6.0	°C/W
Thermal Decistors a lumpitar to Con-	R <sub>(j-c)Q</sub>	SCM1243MF SCM1245MF SCM1246MF	1 element operation (IGBT)	3.0	°C/W
Thermal Resistance, Junction-to-Case		SCM1241M		6.5	°C/W
	R <sub>(j-c)F</sub>	SCM1243MF SCM1245MF SCM1246M	1 element operation (FRD)	4.0	°C/W
Case Operating Temperature	T <sub>OPC</sub>			-20 to 100	°C
Junction Temperature (IGBT)	TJ			150	°C
Storage Temperature	T <sub>stg</sub>			-40 to 150	°C
Isolation Voltage	V <sub>iso</sub>	Between expose	ed thermal pad and each pin; 1 minute, ac	2000	V <sub>rms</sub>

All performance characteristics given are typical values for circuit or system baseline design only and are at the nominal operating voltage and an ambient temperature,  $T_A$ , of 25°C, unless otherwise stated.

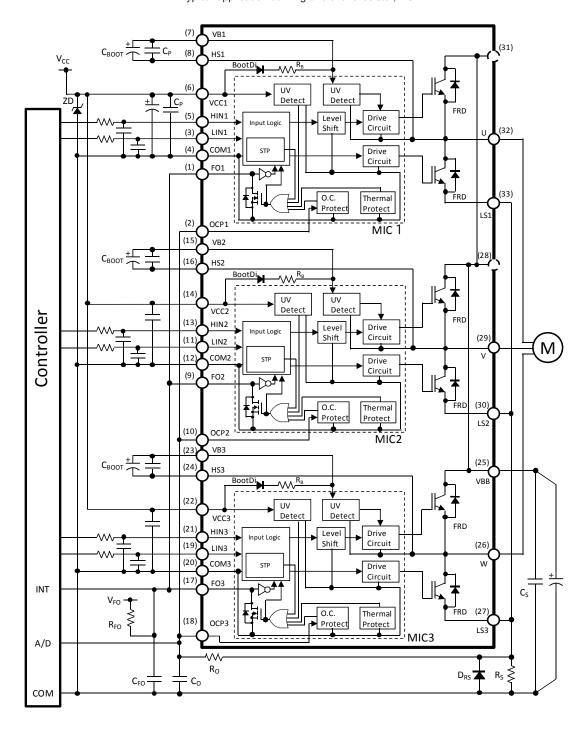
### **Recommended Operating Conditions**

Characteristic	Symbol		Remarks	Min.	Тур.	Max.	Units
Main Supply Voltage	$V_{DC}$	Between VBB	Between VBB and LS		300	400	V
Logic Supply Voltage	V <sub>CC</sub>	Between VCC	and COM	13.5	_	16.5	V
Logic Supply Voltage	V <sub>BS</sub>	Between VB a	nd HS	13.5	_	16.5	V
Minimum Input Pulse Width	t <sub>INmin(on)</sub>	On pulse		0.5	_	_	μs
Minimum input Puise Width	t <sub>INmin(off)</sub>	Off pulse		0.5	_	_	μs
Dead Time*	t <sub>dead</sub>			1.0	_	_	μs
FO Pull-up Resistor	R <sub>FO</sub>			1	_	22	kΩ
FO Pull-up Voltage	V <sub>FO</sub>			3.0	_	5.5	V
Bootstrap Capacitor	Своот			10	_	220	μF
		SCM1241M	For I <sub>P</sub> ≤ 20 A	27	_	-	mΩ
Shunt Resistor	R <sub>S</sub>	SCM1243MF SCM1245MF SCM1246MF	For I <sub>P</sub> ≤ 30 A	15	_	_	mΩ
RC Filter Resistor	Ro			_	_	100	Ω
RC Filter Capacitor	Co			_	_	2200	pF
PWM Carrier Frequency	f <sub>C</sub>			_	_	20	kHz
Junction Temperature	TJ			_	_	125	°C

<sup>\*</sup>Dead Time must be controlled from an external source.

### **Typical Application Diagram**

Typical application utilizing one shunt resistor, RS



See application notes on next page.

### **Notes for Typical Application Diagram**

- To use the OCP circuit shown in the Typical Application drawing, an external shunt resistor, RS, is needed. The RS value depends on how many low-side IGBTs turn on simultaneously.
- To avoid malfunction, the wiring between the LS and COM pins should be as short as possible.
- To prevent surge destruction, put a 0.01 to 1 μF snubber capacitor,
   CS, in parallel with the electrolytic capacitor.
- To prevent surge destruction, put a 18 to 20 V Zener diode between the VCC and COM pins.
- To prevent surge malfunction, put a 0.01 to 0.1 μF ceramic capacitor between the VCC and COM pins and the VB and HS pins.
- To add an external low pass filter, place RO and CO between the A to D pin of the application controller and shunt resistor RS, ensuring that the time constant of this low pass filter is less than 0.2 μs. The internal OCP circuit has a 1.5 μs (min) filtering delay.

- However, the low pass filter causes an additional delay to detecting an overcurrent condition of the SCM1240M, and if the total delay exceeds  $1.7 \mu s$ , permanent damage to the SCM1240M may result.
- To suppress noise, connect a resistor, RF, and capacitor, CF, to the FOx pins. Also, when an overcurrent condition is detected, the FOx pin goes low for 25 μs (typ) as an active low fault flag, and then returns up to its normal state. It is recommended to connect the FOx pin directly to an interrupt pin of the external controller, to ensure the 25 μs interval is detected.
- To provide the best thermal shutdown protection (TSD), it is strongly recommended that the three FOx pins be tied together. In this way an overtemperature event (internal temperature rise above 150°C) in any of the three phases will cause all three phases to shut down. If the FOx pins are not tied together, but are independently pulled up to +5 V, the TSD function for each phase shuts down only that phase.

### ELECTRICAL CHARACTERISTICS, valid at T<sub>A</sub>=25°C, unless otherwise noted

Characteristics	Symbol	Conditions	Min	Тур	Max	Units
Logic Supply Voltage	V <sub>CC</sub>	Between VCC and COM	13.5	_	16.5	V
Logic Supply Current	I <sub>CC</sub>	V <sub>CC</sub> = 15 V, 3 phases operating	_	3	_	mA
Bootstrap Supply Current	I <sub>BS</sub>	VB – HS = 15 V, one phase operating	_	140	_	μA
Inner A Malla ma	V <sub>IH</sub>	V <sub>CC</sub> = 15 V, output on	_	2.0	2.5	V
Input Voltage	V <sub>IL</sub>	V <sub>CC</sub> = 15 V, output off	1.0	1.5	_	V
Input Voltage Hysteresis	V <sub>Ihys</sub>	V <sub>CC</sub> = 15 V	_	0.5	_	V
Institute Occurrent	I <sub>IHH</sub>	V <sub>CC</sub> = 15 V, V <sub>IN</sub> = 5 V	_	230	500	μA
Input Current	I <sub>ILH</sub>	V <sub>CC</sub> = 15 V, V <sub>IN</sub> = 0 V	_	_	2	μA
Hardon alkonol and Out (Hinb Oids)	U <sub>VHL</sub>	V 45.V	10.0	11.0	12.0	V
Undervoltage Lock Out (High Side)	U <sub>VHH</sub>	V <sub>CC</sub> = 15 V	10.5	11.5	12.5	V
	U <sub>VLL</sub>	45.4	10.0	11.0	12.0	V
Undervoltage Lock Out (Low Side)	$U_VLH$	V <sub>CC</sub> = 15 V	10.5	11.5	12.5	V
<del></del>	V <sub>FOL</sub>	V 45VV 5VB 4010	-	-	0.5	V
FO Terminal Output Voltage	V <sub>FOH</sub>	$V_{CC} = 15 \text{ V}, V_{FO} = 5 \text{ V}, R_{FO} = 10 \text{ k}\Omega$		-	_	V
Overcurrent Protection Trip Voltage	$V_{TRIP}$	V <sub>CC</sub> = 15 V	0.46	0.50	0.54	V
Overcurrent Protection Hold Time	t <sub>P</sub>	V <sub>CC</sub> = 15 V	20	25	-	μs
Overtemperature Protection Activation	T <sub>DH</sub>	V <sub>CC</sub> = 15 V		150	165	°C
and Releasing Temperature	$T_DL$			120	135	°C
Blanking Time	t <sub>blank</sub>	V <sub>CC</sub> = 15 V	_	1.65	_	μs
IGBT Breakdown Voltage	V <sub>CES</sub>	V <sub>CC</sub> = 15 V, I <sub>C</sub> = 1 mA, V <sub>IN</sub> = 0 V	600	-	-	V
IGBT Leakage Current	I <sub>CES</sub>	V <sub>CC</sub> = 15 V, V <sub>CE</sub> = 600 V, V <sub>IN</sub> = 0 V	_	_	1	mA
	SCM1241	SCM1241M V <sub>CC</sub> = 15 V, I <sub>C</sub> = 10 A, V <sub>IN</sub> = 5 V	_	1.7	2.2	V
ICDT Caturation Valtage	.,	SCM1243MF V <sub>CC</sub> = 15 V, I <sub>C</sub> = 15 A, V <sub>IN</sub> = 5 V	_	1.7	2.2	V
IGBT Saturation Voltage	V <sub>CE(sat)</sub>	SCM1245MF V <sub>CC</sub> = 15 V, I <sub>C</sub> = 20 A, V <sub>IN</sub> = 5 V	_	1.7	2.2	V
		SCM1246MF   V <sub>CC</sub> = 15 V, I <sub>C</sub> = 30 A, V <sub>IN</sub> = 5 V	_	1.7	2.2	V
		SCM1241M V <sub>CC</sub> = 15 V, I <sub>F</sub> = 10 A, V <sub>IN</sub> = 0 V	_	1.9	2.4	V
Diada Faranad Vallana		SCM1243MF V <sub>CC</sub> = 15 V, I <sub>F</sub> = 15 A, V <sub>IN</sub> = 0 V	_	1.75	2.2	V
Diode Forward Voltage	V <sub>F</sub>	SCM1245MF V <sub>CC</sub> = 15 V, I <sub>F</sub> = 20 A, V <sub>IN</sub> = 0 V	_	1.9	2.4	V
		SCM1246MF V <sub>CC</sub> = 15 V, I <sub>F</sub> = 30 A, V <sub>IN</sub> = 0 V	_	1.5	2.0	V
Diode Recovery Time (Bootstrap)	t <sub>rr</sub>	I <sub>F</sub> = I <sub>RECOVERY(PEAK)</sub> = 100 mA		70	_	ns
Diode Leakage Current (Boot Strap)	I <sub>IB</sub>	V <sub>R</sub> = 600 V	-	_	10	μA
Diode Forward Voltage (Boot Strap)	$V_{FB}$	I <sub>F</sub> = 0.15 A	_	1.1	1.3	V
Diode Series Resistor (Boot Strap)	R <sub>B</sub>		17.6	22.0	26.4	Ω

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### ELECTRICAL CHARACTERISTICS, valid at T<sub>A</sub>=25°C, unless otherwise noted

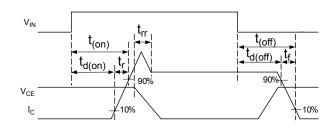
Characteristics	Symbol		Conditions			Max	Units
	t <sub>dH(on)</sub>			_	590	_	ns
	t <sub>rH</sub>			_	80	_	ns
	t <sub>rrH</sub>	SCM1241M	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_C$ = 10 A, inductive load: HIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	_	60	_	ns
	t <sub>dH(off)</sub>		1000, 1111 0 70 1 0 70 1	_	550	_	ns
	t <sub>fH</sub>			_	90	_	ns
	t <sub>dH(on)</sub>			_	600	_	ns
	t <sub>rH</sub>		$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_{C}$ = 15 A, inductive load; HIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	_	70	_	ns
	t <sub>rrH</sub>	SCM1243MF		_	70	_	ns
	t <sub>dH(off)</sub>			_	620	_	ns
High Side Switching Time	t <sub>fH</sub>			_	60	_	ns
Thigh Side Switching Time	t <sub>dH(on)</sub>		$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_{C}$ = 20 A, inductive load; HIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	_	695	_	ns
	t <sub>rH</sub>			_	95	_	ns
	t <sub>rrH</sub>	SCM1245MF		_	75	_	ns
	$t_{\rm dH(off)}$			_	675	_	ns
	t <sub>fH</sub>				55	_	ns
	t <sub>dH(on)</sub>			_	660	_	ns
	t <sub>rH</sub>			_	110	_	ns
	t <sub>rrH</sub>	SCM1246MF	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_C$ = 30 A, inductive load; HIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	_	60	_	ns
	t <sub>dH(off)</sub>		10au, 11114 - 0-75 V 01 3-70 V	_	700	_	ns
	t <sub>fH</sub>				50	_	ns

Continued on the next page...

#### ELECTRICAL CHARACTERISTICS, valid at T<sub>A</sub>=25°C, unless otherwise noted

Characteristics	Symbol	Conditions		Min	Тур	Max	Units
	t <sub>dL(on)</sub>			_	570	_	ns
	t <sub>rL</sub>			_	100	_	ns
	t <sub>rrL</sub>	SCM1241M	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_C$ = 10 A, inductive load: LIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	_	70	_	ns
	t <sub>dL(off)</sub>		1000, 2117 0 70 7 01 0 70 7	_	560	_	ns
	t <sub>fL</sub>			_	100	_	ns
	t <sub>dL(on)</sub>			_	600	_	ns
	t <sub>rL</sub>			_	100	_	ns
	t <sub>rrL</sub>	SCM1243MF	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_{C}$ = 15 A, inductive load; LIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	_	80	-	ns
	t <sub>dL(off)</sub>			_	600	-	ns
Law Cida Cwitabina Tima	t <sub>fL</sub>			_	70	-	ns
Low Side Switching Time	t <sub>dL(on)</sub>	SCM1245MF	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_{C}$ = 20 A, inductive load; LIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	_	715	-	ns
	t <sub>rL</sub>			_	135	_	ns
	t <sub>rrL</sub>			_	115	_	ns
	t <sub>dL(off)</sub>			_	670	_	ns
	t <sub>fL</sub>			_	50	_	ns
	t <sub>dL(on)</sub>			_	660	_	ns
	t <sub>rL</sub>			_	150	_	ns
	t <sub>rrL</sub>	SCM1246MF	$V_{DC} = 300 \text{ V}, V_{CC} = 15 \text{ V}, I_{C} = 30 \text{ A}, \text{ inductive}$ load: LIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	_	70	-	ns
	t <sub>dL(off)</sub>		10au, LIIV - U→3 V 01 3→0 V	_	690	_	ns
	t <sub>fL</sub>				50	_	ns

Switching Timing Definitions



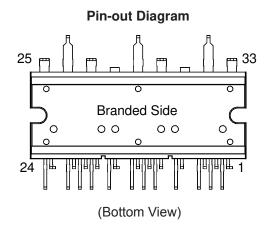
Input-Output Truth Table

Mode	HINx	LINx	High-side MOSFET	Low-side MOSFET
	L	L	Off	Off
Normal <sup>1</sup>	Н	L	On	Off
Norman	L	Н	Off	On
	Н	Н	Off	Off
	L	L	Off	Off
TSD	Н	L	Off	Off
שפו	L	Н	Off	Off
	Н	Н	Off	Off
	L	L	Off	Off
OCP	Н	L	Off	Off
OCP	L	Н	Off	Off
	Н	Н	Off	Off
	L	L	Off	Off
VCCx UVLO <sup>2</sup>	Н	L	Off	Off
VCCX UVLO2	L	Н	Off	Off
	Н	Н	Off	Off
	L	L	Off	Off
\/D <sub>2</sub> , L \/ , O <sub>3</sub>	Н	L	Off	Off
VBx UVLO <sup>3</sup>	L	Н	Off	On
	Н	Н	Off	Off
	L	L	Off	Off
FOx Low	Н	L	Off	Off
FUX LOW	L	Н	Off	Off
	Н	Н	Off	Off

<sup>&</sup>lt;sup>1</sup>In the case where a pair of HINx and LINx signals are asserted at the same time, the shoot-through prevention feature sets both the high-side and the low-side IGBTs off.

<sup>&</sup>lt;sup>2</sup>After the VCCx power rail recovers from a UVLO condition, a rising edge of HINx starts driving the highside IGBT (edge trigger). On the other hand, after the UVLO condition is released, the input level of the LINx pins reflects the state of the low-side IGBTs (level trigger).

<sup>&</sup>lt;sup>3</sup>After the VBx power rail recovers from a UVLO condition, a rising edge of HINx starts driving the high-side IGBT (edge trigger).



### **Terminal List Table**

Name	Number	Function
1	FO <sub>1</sub>	U phase fault output for overcurrent and UVLO detected
2	OCP1	Input for U phase overcurrent protection
3	LIN1	Signal input for low-side U phase (active high)
4	COM1	Supply ground for U phase IC
5	HIN1	Signal input for high-side U phase (active high)
6	VCC1	Supply voltage for U phase IC
7	VB1	High-side floating supply voltage for U phase
8	HS1	High-side floating supply ground for U phase
9	FO <sub>2</sub>	V phase fault output for overcurrent and UVLO detected
10	OCP2	Input for V phase overcurrent protection
11	LIN2	Signal input for low-side V phase (active high)
12	COM2	Supply ground for V phase IC
13	HIN2	Signal input for high-side V phase (active high)
14	VCC2	Supply voltage for V phase IC
15	VB2	High-side floating supply voltage for V phase
16	HS2	High-side floating supply ground for V phase
17	FO3	W phase fault output for overcurrent and UVLO detected
18	OCP3	Input for W phase overcurrent protection
19	LIN3	Signal input for low-side W phase (active high)
20	COM3	Supply ground for W phase IC
21	HIN3	Signal input for high-side W phase (active high)
22	VCC3	Supply voltage for W phase IC
23	VB3	High-side floating supply voltage for W phase
24	HS3	High-side floating supply ground for W phase
25	VBB	Positive DC bus supply voltage
26	W	Output for W phase
27	LS3	Negative DC bus supply ground for W phase
28	VBB	(Pin trimmed) positive DC bus supply voltage
29	V	Output for V phase
30	LS2	Negative DC bus supply ground for V phase
31	VBB	(Pin trimmed) positive DC bus supply voltage
32	U	Output for U phase
33	LS1	Negative DC bus supply ground for U phase

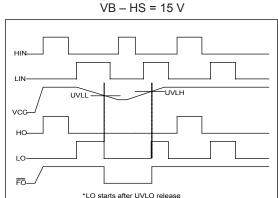
### **Timing Diagrams**

(one phase of three phases)

## High-Side Driver Input/Output and UVLO Protection $V_{CC}$ = 15 $\rm V$

HIN LIN UVHL UVHH

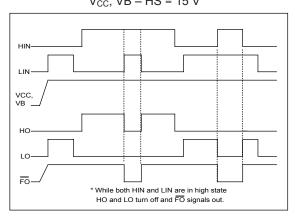
## Low-Side Driver Input/Output and UVLO Protection



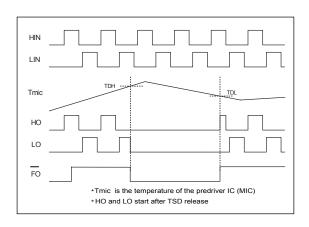
## Shoot-Through Prevention $V_{CC}$ , VB - HS = 15 V

\*No FO output at H-side UVLO

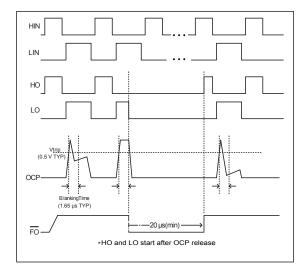
\*HO starts from positive edge after UVLO release



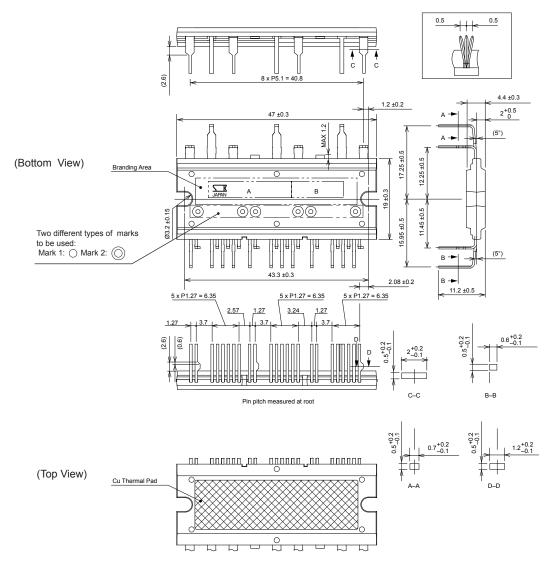
### **Thermal Shutdown**



#### **Overcurrent Protection**



#### PACKAGE OUTLINE DRAWING



Leadform: 2551 (SCM1241M: Fully molded) or

2552 (SCM1243MF, SCM1245MF, SCM1246MF:

Exposed copper thermal pad)

Dimensions in millimeters

The body shall be clean and shall not bear any stain, rust or flaw. The type number and lot number shall be clearly stamped by laser on the body so that cannot be erased easily.

Branding codes

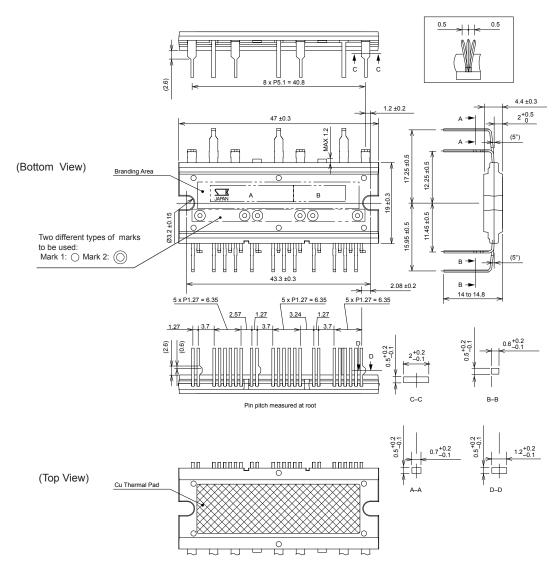
(exact appearance at manufacturer discretion): Section A, type: SCM124xMF or SCM1241M

Section B, lot: YMDDT

Where: Y is the last digit of the year of manufacture M is the month (1 to 9, O, N, D) DD is the date

T is the tracking letter (A to Z)

Device composition complies with the RoHS directive.



Leadform: 2557 (SCM1241M: Fully molded) or (SCM1243MF, SCM1245MF, SCM1246MF:

Exposed copper thermal pad)

Dimensions in millimeters

The body shall be clean and shall not bear any stain, rust or flaw. The type number and lot number shall be clearly stamped by laser on the body so that cannot be erased easily.

Branding codes

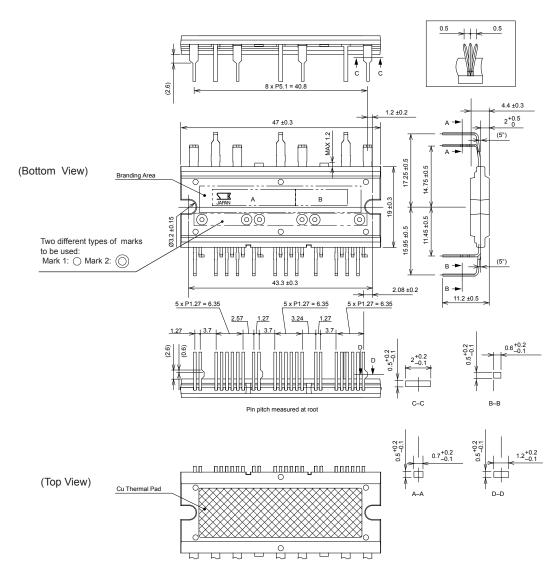
(exact appearance at manufacturer discretion): Section A, type: SCM124xMF or SCM1241M

Section B, lot: YMDDT

Where: Y is the last digit of the year of manufacture M is the month (1 to 9, O, N, D) DD is the date

T is the tracking letter (A to Z)

Device composition complies with the RoHS directive.



Leadform: 2558 (SCM1241M: Fully molded) or (SCM1243MF, SCM1245MF, SCM1246MF:

Exposed copper thermal pad)

Dimensions in millimeters

The body shall be clean and shall not bear any stain, rust or flaw. The type number and lot number shall be clearly stamped by laser on the body so that cannot be erased easily.

Branding codes

(exact appearance at manufacturer discretion): Section A, type: SCM124xMF or SCM1241M

Section B, lot: YMDDT

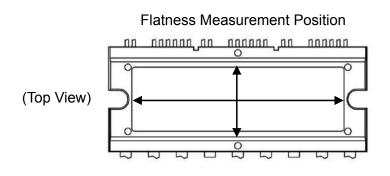
Where: Y is the last digit of the year of manufacture M is the month (1 to 9, O, N, D)
DD is the date

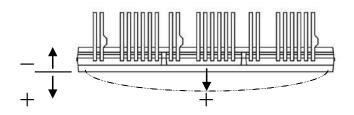
T is the tracking letter (A to Z)

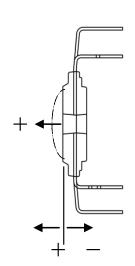
Device composition complies with the RoHS directive.

### **MECHANICAL CHARACTERISTICS**

Characteristic	Remarks	Min.	Тур.	Max.	Units
Heataink Mounting Sarow Targue	Use one M3 screw each end	58.8	ı	78.4	N•cm
Heatsink Mounting Screw Torque	Ose one was screw each end	6.0	ı	8.0	kgf•cm
Flatness of Heatsink Attachment Area	Refer to figure below	0	ı	200	μm
Dockogo Weight	SCM1241M	-	10.8	-	g
Package Weight	SCM124xMF	_	11.8	-	g

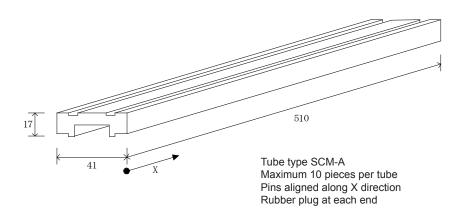


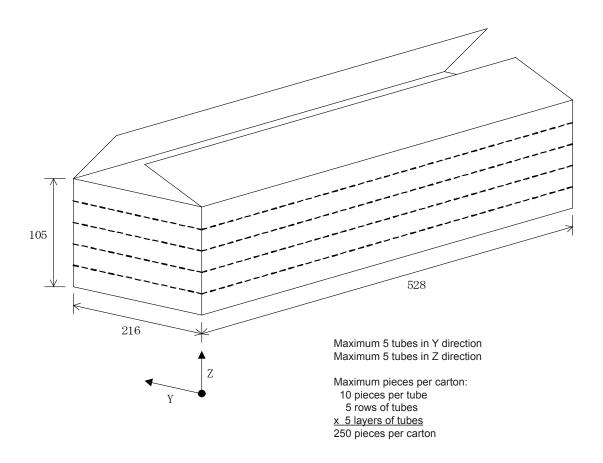


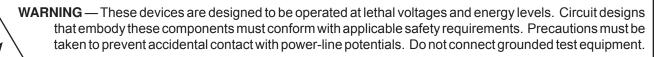


### **PACKING SPECIFICATION**

Dimensions in millimeters







The use of an isolation transformer is recommended during circuit development and breadboarding.

Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

#### **Cautions for Storage**

- Ensure that storage conditions comply with the standard temperature (5°C to 35°C) and the standard relative humidity (around 40 to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of product that has been stored for a long time.

#### **Cautions for Testing and Handling**

- When tests are carried out during inspection testing and other standard test periods, protect the product from power surges from the testing device, shorts between adjacent product packages, and shorts to the heatsink.
- The screwing torque for attaching a heatsink shall be 58.8 to 78.4 N•cm (6.0 to 8.0 Kgf•cm).
- Ensure there are no foreign objects between the heatsink and thermal pad; only silicone thermal grease is allowed.

#### Remarks About Using Silicone Grease with a Heatsink

- When silicone grease is used in mounting this product with a heatsink, grease shall be applied evenly and thinly. If more silicone grease than required is applied, it may produce stress.
- Volatile-type silicone greases may permeate the product and produce cracks after long periods of time, resulting in reduced heat radiation effect, and possibly shortening the lifetime of the product.
- Hard silicone greases may cause cracks in the product when screwing the product to a heatsink.

 Our recommended silicone greases for heat radiation purposes, which will not cause any adverse effect on the product life, are indicated below:

_	Type	Suppliers
	G746	Shin-Etsu Chemical Co., Ltd.
	YG6260	Momentive Performance Materials Holding, Inc.
	SC102	Dow Corning Toray Silicone Co., Ltd.

#### Soldering

 When soldering the product, please be sure to minimize the working time, within the following limits:

260±5°C 10 s 380±5°C 5 s

 Soldering iron should be at a distance of at least 1.5 mm from the body of the product

#### **Electrostatic Discharge**

- When handling the product, operator must be grounded. Grounded wrist straps worn should have at least 1 MΩ of resistance to ground to prevent shock hazard.
- Workbenches where the product is handled should be grounded and be provided with conductive table and floor mats.
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the product, the head of soldering irons or the solder bath must be grounded in other to prevent leak voltages generated by them from being applied to the product.
- The product should always be stored and transported in our shipping containers or conductive containers, or be wrapped in aluminum foil.

- The contents in this document are subject to changes, for improvement and other purposes, without notice. Make sure that this is the latest revision of the document before use.
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- (T<sub>J</sub>) affects the reliability significantly.
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